Theoretical Analysis of Electronic Structure for the Chemical Bonding of Pu and Am in MgO

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The relativistic discrete-variational Dirac-Fock-Slater (DV-DFS) method was performed to investigate the electronic structure of MgO doped with Pu or Am atoms. The differences between these systems, in particular, the participation of *d*-electrons and *f*-electrons in chemical bonding, were clarified by calculating their electronic structures. Substitution of actinide atoms was found to result in the effective charges of MgO becoming smaller, with a large charge transfer occurring as far as the second layer. It was also found that the bonding feature between the center atom and the surrounding oxygen atoms was extended to lower energy in the case of actinide (An) substituted systems. Moreover, the bonding characteristics were assigned; a bonding interaction for An6*d*-O2*p* and an anti-bonding for An5*f*-O2*p* near the HOMO level. These complex effects were found to dominate the strength of the covalent bonding between MgO and actinide atoms.

1. Introduction

The electronic structures of metal oxides containing actinide atoms give essential information on the interaction between the actinide atoms and base metal oxides. In the field of nuclear technology and science, magnesium oxide,¹⁻⁴ zirconium oxide,^{4,5} and spinel^{6, 7} are appropriate candidates for an inert matrix, which acts as a mechanical support and diluent, used in transmutation of actinides (An), such as plutonium (Pu) and americium (Am).⁸ Early study⁹ indicated that magnesium oxide (MgO) was considered to be the most appropriate support material for transmutation of Am because of its desirable properties, such as high melting point, relatively high thermal conductivity and high mobility of helium.¹⁰ Researches of the thermophyisical properties of doped actinides in metal oxides are accumulated so far, however less work has focused on the electronic structures and chemical bonding nature of these systems to understand the physical and chemical properties.

The electronic configurations of the actinides also provide insight into the properties of their compounds. The difference between the electronic configuration of neutral Pu and Am atoms is only one *f*-electron (Pu: $5f^{6}6d^{0}7s^{2}7p^{0}$, Am: $5f^{7}6d^{0}7s^{2}7p^{0}$); however, the f-electrons of lighter actinides (Pa-Pu) are considered to have an itinerant trend,^{11, 12} on the other hand, the felectrons of transplutonium elements (Am-Cf) have localized character and behave more like the lanthanides. It is known that a boundary of the chemical and physical properties lies between Pu and Am.¹³ For example, Np and Pu metals have the unique properties; such as low-symmetry of crystal structure (monoclinic) at room temperature, low melting point, and multiple phase transition. On the other hand, transplutonium metals have more symmetric hexagonal close-packed structure and relatively higher melting point than Np and Pu. Furthermore, a large variation in stoichiometry is found in the actinide oxides. The sesquioxide becomes the predominate oxide for the transplutonium elements, in contrast to the lighter actinides prefer to have higher valence.

The present study is undertaken with the goal of advancing our understanding of fundamental chemical bonding between actinide atom and metal oxides. The relativistic discrete-variational Dirac-Fock-Slater (DV-DFS) method was applied to investigate the electronic structure of MgO doped with Pu or Am atoms. This method gives reliable information of chemical bonding even for heavy system such as the actinide series. Although there are several theoretical studies of pure actinide oxides,¹⁴⁻¹⁸ the interaction between actinide atoms and an inert matrix has not been well clarified until now. The current investigation focused on the difference between these systems, in particular, the participation of *d*-electrons and *f*-electrons in the chemical bonding.

2. Computational Method

The DV-DFS molecular orbital (MO) method, based on the Dirac-Fock-Slater (DFS) approximation, was used to perform cluster calculations of pure MgO and actinide doped MgO. This method provides a powerful tool for the study of the electronic structure of molecules and solids containing heavy elements.^{14, 16, 19-23} The detailed procedure has been published elsewhere.²⁴⁻²⁶

The schematic representation of a model cluster of MgO is shown in Figure 1. MgO has NaCl structure and all bond length



Figure 1. Model cluster for this study $(5 \times 5 \times 4 \text{ atoms with } 1352 \text{ point charges})$. An(Pu or Am) atom substituted for the center Mg₁.

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Figure 2. Magnification of a part of model cluster. The center Mgr was substituted by Pu or Am atom.

between Mg and O is fixed to 210.6 pm. The calculation, when performed for insulators such as magnesium oxides, is difficult because of the long-range Coulomb interactions even from distant atoms. In order to represent the effect, 1352 points of +2 and -2 point charges (PC) were placed at the lattice positions around the cluster model. These PC guaranteed that the Madelung potential inside the cluster was properly reproduced. Figure 2 shows a part of the model cluster, cutting away the substituted center atom and surrounding atoms from Figure 1. The Pu or Am doped MgO system was also calculated, using the model cluster with substitution of an An atom for the center Mg₁ atom as shown in Figure 2. For the initial charge, An atoms were assigned as trivalent and the other atoms as divalent, in other words, the electronic configurations were Pu: $5f^{5}6d^{0}7s^{0}7p^{0}$, Am: $5f^{6}6d^{0}7s^{0}7p^{0}$, Mg: $2s^{2}2p^{6}3s^{0}3p^{0}$, and O: $2s^22p^63s^03p^0$. The bond length of Pu-O₂ and Am-O₂ were estimated from the ionic radius of the trivalent atom, and were determined to be 238.39 pm and 235.91pm, respectively. The lattice relaxation caused by An substitution was not considered in the present calculation, therefore, only the bond lengths between metals (Mg₁, Pu, or Am) and adjacent oxygens (O₁, O₂) were changed.

3. Results and Discussion

3.1. Effective Charge and Ionic Interaction. Table 1 shows the effective charges on substituted Pu (Pu+MgO), Am (Am+MgO) and the surrounding Mg and O with reference to the pure MgO (Mg+MgO). The positions of these atoms are indicated in Figure 2. The Mulliken population analysis²⁷ is known to have a basis set dependence; however, the analysis provides qualitative aspects of the chemical bonding. In this calculation, numerical basis sets²⁸ were generated for Pu, Am, Mg, and O atoms, with the same conditions, so that the effect of the basis set on the orbital population was negligible. As shown in Table 1, the effective charges of Mg and O became fairly small in consequence of the An substitution, and a large charge transfer to the second layer occurred. Plutonium has a slightly larger effective charge (0.53) than Am (0.50) and this indicates that Pu prefers

 TABLE 1: Effective Charge of Center Atom (Mg1, Pu, or Am) and Neighbor Mg and O

	Mg+MgO	Pu+MgO	Am+MgO
$Mg(An)_1$	0.71	0.53	0.50
Mg_2	0.72	0.37	0.38
Mg_3	0.64	0.28	0.29
O_1	-0.74	-0.21	-0.23
O_2	-0.70	-0.25	-0.26
O ₃	-0.72	-0.37	-0.38

to have a higher oxidation state than Am. It is known that MgO is a strongly ionic system, and therefore the HOMO-LUMO gap of Mg+MgO is calculated as 4.18 eV; however, that of the Pu+MgO (0.55 eV) and Am+MgO (0.02 eV) systems were found to be small in this study. This indicates that the ionic bonding strength becomes weak and the systems become unstable as a result of An substitution.

Table 2 shows the occupation number of the valence orbitals for the Mg+MgO, Pu+MgO, and Am+MgO systems. When comparing the final orbital occupations with the initial ones, the number of electrons of Mg3s, Mg3p, An6d, An7s, and An7p orbitals increase and only that of the 5f orbital slightly decrease. A significant change in the orbital population was observed in the increase of the 6d electron for the An+MgO system. The Pu6d orbital receives 1.84 electrons from the surrounding oxygen atoms, while the Am6d orbital receives 1.79 electrons. It follows from these results that the number of electrons in the 5f orbital is directly proportional to the atomic number, but that of the 6d orbital is inversely proportional in the MgO environment. The occupation numbers of O2s and O2p become smaller with An substitution. The O_12s , O_12p , O_22s , and O_22p orbitals release 0.07, 0.47, 0.05, and 0.40 electrons, respectively, in the Pu+MgO system, and 0.06, 0.46, 0.05, and 0.40, respectively, in the Am+MgO system. This indicates that charge transfer occurs mainly from the O2p oribtal to An6d orbital. The occupation of the Pu6d orbital is larger than that of Am6d, however, the total charge transfer between Am and the surrounding oxygen (+2.50), and also that for Pu (+2.46).

3.2. Analysis of Covalent Bonding. In order to evaluate covalent interactions between substituted Pu, Am, and the surrounding oxygens, bond overlap population (BOP) analyses were obtained, as shown in Table 3. After substitution of An for Mg, the interaction between the An atom and the surrounding oxygen (O_1, O_2) becomes larger than that for Mg. The BOP for Pu+MgO is slightly larger than Am+MgO. On the other hand, the bonding of Mg₂-O₁, Mg₃-O₁, and Mg₃-O₂ becomes weak, because electrons move to the surrounding of An and a strong interaction between An and oxygen is generated by An substitution.

TABLE 2: Orbital Occupations of Valence Orbitals

	Mg+MgO		Pu+MgO	Am+MgO
		An 5f _{5/2}	3.90	4.74
		An 5f _{7/2}	0.95	1.16
		An $6d_{3/2}$	0.77	0.75
		An $6d_{5/2}$	1.07	1.04
$Mg_1 3s$	0.48	An 7s	0.39	0.40
$Mg_1 \beta p_{1/2}$	0.27	An 7 <i>p</i> _{1/2}	0.22	0.23
$Mg_1 \beta p_{3/2}$	0.54	An $7p_{3/2}$	0.20	0.21
$O_1 2s$	1.80	$O_1 2s$	1.73	1.74
$O_1 2 p_{1/2}$	1.65	$O_1 2 p_{1/2}$	1.50	1.50
$O_1 2p_{3/2}$	3.29	$O_1 2p_{3/2}$	2.97	2.98
O ₂ 2s	1.78	$O_2 2s$	1.73	1.73
$O_2 2p_{1/2}$	1.64	$O_2 2p_{1/2}$	1.51	1.51
$O_2 2p_{3/2}$	3.28	${ m O}_2 2 p_{3/2}$	3.01	3.01

TABLE 3: Bond Overlap Population between Center Atom(Mg1, Pu, or Am) and Neighbor Oxygen (O1, O2)

	Mg+	-MgO	Pu+	MgO	Am+MgO		
	O_1	O_2	O_1	O_2	O_1	O ₂	
$Mg(An)_1$	0.32	0.26	0.55	0.39	0.54	0.38	
Mg_2	0.65	-0.20	0.46	-0.10	0.47	-0.10	
Mg_3	0.24	1.23	0.18	1.03	0.20	1.04	

TABLE 4: Orbital Overlap Population between Valence Orbital of Center Atom (Mg₁, Pu, or Am) and O₁ and O₂

Mg+MgO				Pu+MgO					Am+MgO				
	$O_1 2s$	$O_1 2p$	$O_2 2s$	$O_2 2p$		$O_1 2s$	$O_1 2p$	$O_2 2s$	$O_2 2p$	$O_1 2s$	$O_1 2p$	$O_2 2s$	$O_2 2p$
					An 5f	0.01	0.10	0.00	0.02	0.01	0.08	0.00	0.01
					An 6d	0.05	0.28	0.01	0.09	0.05	0.27	0.01	0.09
Mg ₁ 3s	-0.01	0.12	0.00	0.06	An 7s	0.01	0.07	0.01	0.05	0.01	0.07	0.01	0.05
Мg ₁ <i>3р</i>	0.07	0.16	0.01	0.06	An 7p	0.10	0.07	0.01	0.03	0.11	0.07	0.01	0.03

The analysis of orbital contributions to the chemical bonding is useful to understand the nature of 6d and 5f electrons in the actinide systems. Table 4 provides the orbital overlap populations between the valence orbitals of $An-O_1$ and $An-O_2$. The main difference between the Pu+MgO and Am+MgO systems are the An5f-O2p and An6d-O2p orbital overlap populations. Both of the orbital overlap populations for Pu5f-O2p and Pu6d-O2p are larger than those for Am5f-O2p and Am6d-O2p. This causes a larger interaction between Pu and O₁, than that for Am; however such a discrepancy is obscure in the case of An and O_2 . As indicated in Table 2, the number of 6d electrons directly influences the An6d-O2p orbital overlap population, however the influence of 5f occupation reveals an opposite trend. In order to sufficiently examine the contribution of 6dand 5f orbitals toward chemical bonding, the participation of the valence orbitals was analyzed for bonding features.

Figure 3 illustrates the bonding features of the central Mg atom with neighboring O1 or O2 for the Mg+MgO system versus the molecular orbital (MO) energy. The figures consist of the calculated partial density of states (PDOS) for O2p, Mg3s, and Mg3p, which are main components of the valence band, together with the BOP between Mg and O1 or O2. Vertical lines shown in the figures of PDOS are the energy levels of each component. In these figures, the HOMO level, was calibrated to be 0 eV, and positive and negative values of the BOP signify bonding and anti-bonding features, respectively, for the corresponding MO. The valence band of Mg+MgO contains mainly an O2p component plus some components of Mg3p and Mg3s, implying that Mg+MgO is a strongly ionic system. From these figures, the bonding features show a similar trend to the PDOS for the O2porbital in both the Mg-O₁ and Mg-O₂ cases. Moreover, the strengths of covalent bonding for Mg-O1 and Mg-O2 are almost the same, although the dominant bonding features appear at different energy levels.

The principal features of BOP and PDOS of corresponding energy are indicated as arrows and categorize into five parts. The small Mg3p orbital is distributed from the HOMO to



Figure 3. Bond overlap population of Mg₁-O₁ and Mg₁-O₂. **a**, **b**: Mg3*p*-O2*p* interaction, **c**: Mg3*s*-O2*p* interaction, **d**: Mg3*s*-Mg3*p*-O2*p* hybridization and **e**: Mg3*p*-O2*p* and Mg3*p*-O2*p* interaction

about -1.5 eV, and has bonding interaction (**b**) with the O2*p* orbital, while anti-bonding interaction indicated as feature (**a**) is predominant around the HOMO level. The Mg3*s* orbital appears from about -1.5 eV, and has bonding interaction (**c**) with the O2*p* orbital in Mg-O₁ and in Mg-O₂. The Mg3*p* and the Mg3*s* orbitals are hybridized from about -2.5 to -3.5 eV, and have bonding interaction (**d**) with the O2*p* orbital. The Mg3*p* and the Mg3*s* orbitals appear again from approximately -3.5 eV and -5.0 eV, respectively, and have bonding interaction (**e**) with the O2*p* orbital. It is noted that almost all interactions of O2*p*-Mg3*s*, O2*p*-Mg3*p*, and O2*p*-Mg3*s*-Mg3*p* indicate bonding features, but the MO close to the HOMO level shows anti-bonding features, which appear clearly in the bonding of Mg-O₂, than that of Mg-O₁.

The valence band of the Pu+MgO system mainly contains an O2p component plus some Pu5f and Pu6d components. The PDOS of O2p, Pu5f, and Pu6d together with the BOP between Pu and O_1 or O_2 are illustrated in Figure 4. From these figures, it can be presumed that almost all bonding features mainly consist of Pu6d-O2p interactions. The O_12p and O_22p orbitals appear around 3.0 eV deeper in energy than the case of Mg+ MgO, with the shift caused by the charge transfer between Pu and oxygen. The covalent bonding of Pu-O1 becomes stronger than that of Pu-O₂, and consequently, the reinforcement of lateral bonding arises from Pu substitution for Mg. The orbital interaction can be approximately divided into three parts, as shown in these figures. The large components of Pu5f are distributed around the HOMO, and have anti-bonding interaction (a) with the O2p orbital in $Pu-O_2$. The Pu5f and Pu6dorbitals are distributed from about -0.5 to -6.5 eV, and interact with the O2p orbital in both bonding and anti-bonding characteristics (b). The Pu5f, Pu6d, and O2p orbitals are well hybridized and the largest BOP in Pu-O₂ is due to this hybridization. The Pu6d orbital is also distributed from about -6.5 to -8.0 eV, and interacts with the O2p orbital as large bonding features (c), as shown in Figure 4. The overlap of the O2p and Pu6d orbitals becomes large, because of the shift of O2p orbitals toward



Figure 4. Bond overlap population of Pu-O₁ and Pu-O₂.
a: Pu5f-O2p interaction, b: Pu5f-Pu6d-O2p hybridization and c: Pu6d-O2p interaction



Figure 5. Bond overlap population of Am-O₁ and Am-O₂.
 a: Am5f-O2p interaction, b: Am5f-Am6d-O2p hybridization and c: Am6d-O2p interaction

lower energy, which was caused by the charge transfer between Pu and oxygen, and consequently, a largest bonding feature arises. From these results, it has been clarified that O2p-Pu6*d* interaction plays an important role for the bonding of Pu-O₁ and Pu-O₂.

The PDOS of O2p, Am5f, and Am6d, for the Am+MgO system, together with the BOP between Am and O_1 or O_2 , are shown in Figure 5. The valence band of the Am+MgO system, like Pu+MgO, mainly contains an O2p component plus some Am5f and Am6d components, and the general trends are nearly similar to the Pu+MgO system. In order to analyze the discrepancy between these two systems, the principal features of BOP and PDOS of corresponding energy were indicated as arrows for the Am+MgO. The orbital interaction can be divided into three parts. The large components of the Am5f orbital are distributed from the HOMO to -1.0 eV, and have anti-bonding interaction (a) with the O2p orbital. The Am5f and Am6d orbitals are distributed from -1.0 to -6.5 eV, and interact toward the O2p orbital with both bonding and anti-bonding characteristics (b). The Am5f, Am6d, and O2p orbitals are well hybridized, however these hybridized MOs are fewer than those of the Pu system. The hybridization also produces the largest bonding feature in Am-O2, while it contributes a small anti-bonding feature in Am-O1. The Am6d orbital is distributed from -6.55 to -8.0 eV, and has bonding interaction (c) with the O2p orbital. The intensity of the O2p-Am6d interaction is similar to that of O2p-Pu6d, however the orbital occupation of Am6d is less than that of Pu6d, as shown in Table 2. That is, Am-O₁ and Am-O₂ interactions are weaker than those of Pu-O₁ and Pu-O₂. The most important difference between the Pu+MgO and Am+MgO systems is the electronic structures around the Fermi energy, which are assigned to O2p-An5f interaction. Apparently, the overlap of Am5f-O2p is larger than that for Pu, in proportion to the orbital occupation of An5f, but this interaction has anti-bonding characteristic, and therefore the chemical bonding for Am-O1 and Am-O2 is weaker than that for Pu-O₁ and Pu-O₂.

Consideration of the charge density of an ideally isolated ion is subtracted from that of the cluster (the difference in charge density) of the interatomic region can provide additional insight into clarifying the covalent bonding in these systems.²⁹ The difference in charge densities of Pu-O₁ and Am-O₁ are shown in Figure 6, compared with those of Mg₁-O₁. The Mg, Pu, and Am atomic positions are at r = 0.0 pm, and O₁ is at r = 210.6 pm. From the difference in charge density of Mg₁-O₁, no electrons binding two nuclei are exhibited to generate covalent bonding.



Figure 6. Cross sectional view of the difference in charge density for $Pu-O_1$ and $Am-O_1$ comparing with Mg_1-O_1 . Atomic unit (au) is Bohr radius, which corresponds to 52.9 pm.

On the other hand, the charge densities for the Pu-O₁ and Am-O₁ bonds increase in the interatomic region. The difference in the charge densities of Mg, Pu, and Am are 0.004, 0.021 and 0.020 at the ionic radius of the metal atom (Pu(III) = 114.0 pm, Am(III) = 111.5 pm, Mg(II) = 86.0 pm),³⁰ respectively. This indicates that ionic bonding dominates the chemical bonding of Mg₁-O₁, and covalent bonding dominates in the chemical bonding of An-O₁. In the case of An-O₁, increases of the difference in charge density inside the An atoms are appreciable. The increase implies that the An5*f* electron participates in shielding the nuclear charge, which makes the effective charge of the An atom small. Moreover, a remarkable discrepancy between the bonding nature of Pu-O₁ and Am-O₁ is recognized in this shielding.

4. Conclusions

In order to investigate the electronic structure of MgO doped with Pu or Am atoms, the relativistic discrete-variational Dirac-Fock-Slater (DV-DFS) method was performed. It was found that the effective charges of Mg and O become small, in consequence of the An substitution, in addition to a large charge transfer that reached to the second layer. Furthermore, the effective charge of Pu (0.53) and Am (0.50) indicated that Pu prefers to have a higher oxidation state than Am. Using a combination of PDOS for the main components of the valence band of the Mg+MgO, Pu+MgO, and Am+MgO systems, and the BOP between the Metal (Mg, Pu, or Am)-O1 and Metal-O2 versus the MO energy, the contribution of these atomic orbitals to the chemical bonding was clarified. In the case of the Mg+MgO system, almost all interactions for O2p-Mg3s, O2p-Mg3p, and O2p-Mg3s-Mg3p exhibited bonding features, although those for O2p-Mg3p near the HOMO level showed anti-bonding features. Conversely, in the case of the An+MgO system, the largest bonding feature is produced from interactions of An6d-O2p, and the reinforcement of lateral bonding occurred by an An substitution for Mg. One of the essential results of this calculation is the interpretation of the chemical bonding nature of An doped MgO. The interaction of An6d-O2p plays an important role, however, that of An5f-O2p is also effective for determining the bonding strength between An and the surrounding oxygens, because of their anti-bonding feature. Furthermore, it was revealed that the strength of both the ionic and covalent bonding are stronger in the Pu+MgO system than the Am+MgO system, and these results implied that the stability of Pu in MgO is higher than Am in MgO. The difference in the charge density of An-O1 exhibited an increase in density inside the An atoms, which implied a contribution of the An5f electron in screening the charges. In the present study, the participation of d- and f-electrons in chemical bonding was evaluated, and the results suggest that charge screening occurred due to An5f electrons.

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